EL5134, EL5135, EL5234, EL5235



PRELIMINARY

Data Sheet

December 15, 2003

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FN7383.1
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630MHz, Gain of 5, Low Noise Amplifiers

élantec.

The EL5134, EL5135, EL5234, and EL5235 are ultra-low voltage noise, high speed voltage feedback

amplifiers that are ideal for applications requiring low voltage noise, including communications and imaging. These devices offer extremely low power consumption for exceptional noise performance. Stable at gains as low as 5, these devices offer 100mA of drive performance. Not only do these devices find perfect application in high gain applications, they maintain their performance down to lower gain settings.

These amplifiers are available in small package options (SOT-23) as well as the MSOP and the industry-standard SO packages. All parts are specified for operation over the -40°C to +85°C temperature range.

Ordering Information

PART NUMBER	PACKAGE	TAPE & REEL	PKG. DWG. #	
EL5134IS	8-Pin SO	-	MDP0027	
EL5134IS-T7	8-Pin SO	7"	MDP0027	
EL5134IS-T13	8-Pin SO	13"	MDP0027	
EL5135IW-T7	5-Pin SOT-23	7" (3K pcs)	MDP0038	
EL5135IW-T7A	5-Pin SOT-23	7" (250 pcs)	MDP0038	
EL5234IY	10-Pin MSOP	-	MDP0043	
EL5234IY-T7	10-Pin MSOP	7"	MDP0043	
EL5234IY-T13	10-Pin MSOP	13"	MDP0043	
EL5235IS	8-Pin SO	-	MDP0027	
EL5235IS-T7	8-Pin SO	7"	MDP0027	
EL5235IS-T13	8-Pin SO	13"	MDP0027	

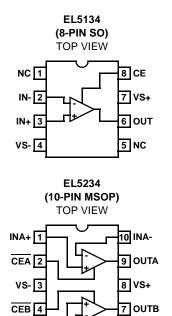
Features

- 650MHz -3dB bandwidth
- Ultra low noise 1.9nV/√Hz
- 450V/µs slew rate
- Low supply current = 7.3mA
- Single supplies from 5V to 12V
- Dual supplies from ±2.5V to ±5V
- Fast disable on the EL5134 and EL5234
- Duals EL5234 and EL5235
- Low cost

Applications

- Imaging
- Instrumentation
- Communications devices

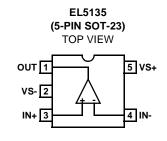
Pinouts



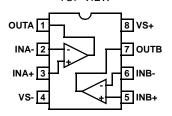
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6 INB-

INB+ 5



EL5235 (8-PIN SO) TOP VIEW



Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Supply Voltage from V_S + to V_S
I _{IN} -, I _{IN} +, CE
Continuous Output Current
Power Dissipation See Curves

Storage Temperature6	5°C to +125°C
Operating Temperature	40°C to +85°C
Operating Junction Temperature	+125°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$

$\label{eq:expectations} Electrical Specifications \qquad V_{S} + = +5V, \ V_{S} - = -5V, \ R_{L} = 150\Omega, \ R_{F} = 900\Omega, \ R_{G} = 100\Omega, \ T_{A} = 25^{\circ}C, \ unless \ otherwise \ specified.$

PARAMETER	DESCRIPTION	CONDITIONS	MIN	ТҮР	MAX	UNIT
V _{OS}	Offset Voltage		-1	0.2	1	mV
T _C V _{OS}	Offset Voltage Temperature Coefficient	Measured from T _{MIN} to T _{MAX}		-0.8		µV/°C
IB	Input Bias Current	V _{IN} = 0V	2.5	3.7	5.5	μA
I _{OS}	Input Offset Current	V _{IN} = 0V	-0.7	0.3	0.7	nA
T _C I _{OS}	Input Bias Current Temperature Coefficient	Measured from T_{MIN} to T_{MAX}		-3		nA/°C
PSRR	Power Supply Rejection Ratio	V_{S} + = 4.75V to 5.25V	75	85		dB
CMRR	Common Mode Rejection Ratio	$V_{CM} = 0V \text{ to } 3.8V$	80	108		dB
CMIR	Common Mode Input Range	Guaranteed by CMRR test	±3	±3.3		V
R _{IN}	Input Resistance	Common mode	5	16		MΩ
C _{IN}	Input Capacitance			1		pF
IS	Supply Current		5.6	6.7	7.8	mA
AVOL	Open Loop Gain	$R_L = 1k\Omega$ to GND	4.0	8.0		kV/V
V _O	Voltage Swing	R_L = 1kΩ, R_F = 900Ω, R_G = 100Ω	±3.5	3.9		V
		R_L = 150Ω, R_F = 900Ω, R_G = 100Ω	±3.3	3.65		mV
I _{SC}	Short Circuit Current	$R_L = 10\Omega$	70	140		mA
BW	-3dB Bandwidth	$A_V = +10, R_L = 1k\Omega$		600		MHz
BW	±0.1dB Bandwidth	$A_V = +10, R_L = 1k\Omega$		120		MHz
GBWP	Gain Bandwidth Product			1500		MHz
PM	Phase Margin	$R_L = 1k\Omega, C_L = 6pF$		55		0
SR	Slew Rate	V_{S} = +5V, R_{L} = 150 Ω , V_{OUT} = 0V to 3V	350	475		V/µs
t _R , t _F	Rise Time, Fall Time	±0.1V _{STEP}		TBD		ns
OS	Overshoot	±0.1V _{STEP}		TBD		%
t _{PD}	Propagation Delay	±0.1V _{STEP}		TBD		ns
t _S	0.01% Settling Time			TBD		ns
	0.01% Settling Time			14		ns
dG	Differential Gain	$A_V = 2, R_F = 1k\Omega$		0.01		%
dP	Differential Phase	$A_V = 2, R_F = 1k\Omega$		0.01		o
e _N	Input Noise Voltage	f = 10kHz		1.9		nV/√Hz
i _N	Input Noise Current	f = 10kHz		0.9		pA/√Hz

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